G8551 PNP EPITAXIAL TRANSISTOR

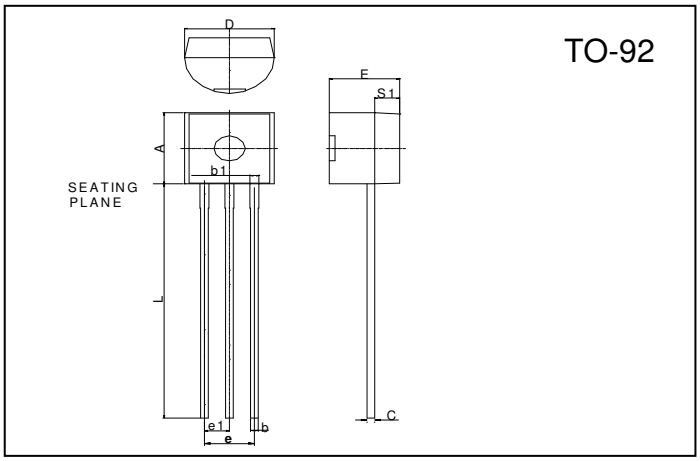
Description

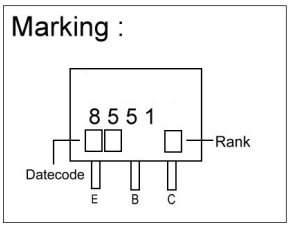
The G8551 is designed for use in 2W output amplifier of portable radios in class B push-pull operation.

Features

*High Collector current (IC: 1.5A)
*Complementary to G8051

Package Dimensions





REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (Ta = 25℃,unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collect Current	I_C	-1.5	A
Base Current	I_B	-0.5	A
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-55 ~ +150	℃
Total Power Dissipation	P_D	1	W

Electrical Characteristics(Ta = 25℃,unless otherwise specified)

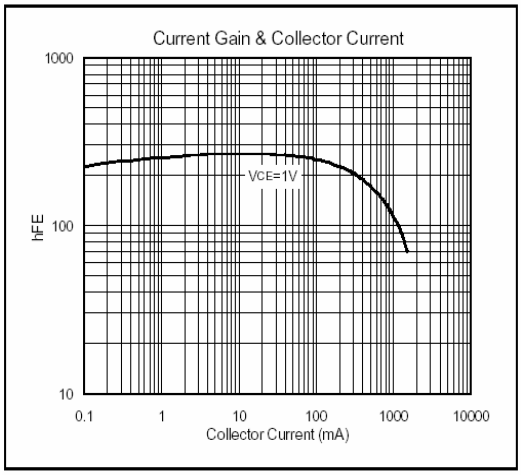
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-40	-	-	V	I_C=-100uA
BV_{CEO}	-25	-	-	V	I_C=-2mA
BV_{EBO}	-6	-	-	V	I_E=-100uA
I_{CBO}	-	-	-100	nA	V_{CB}=-35V
I_{EBO}	-	-	-100	nA	V_{BE}=-6V
*$V_{CE(sat)}$	-	-	-0.5	V	I_C=-800mA, I_B=-80mA
*$V_{BE(sat)}$	-	-	-1.2	V	I_C=-800mA, I_B=-80mA
*$V_{BE(on)}$	-	-	-1	V	V_{CE}=-1V, I_C=-10mA
*$h_{FE}1$	45	-	-		V_{CE}=-1V, I_C=-5mA
*$h_{FE}2$	120	-	500		V_{CE}=-1V, I_C=-100mA
*$h_{FE}3$	40	-	-		V_{CE}=-1V, I_C=-800mA
fT	100	-	-	MHz	V_{CE}=-10V, I_C=-50mA, f=100MHz
Cob	-	9	-	pF	V_{CB}=-10V, I_E=0, f=1MHz

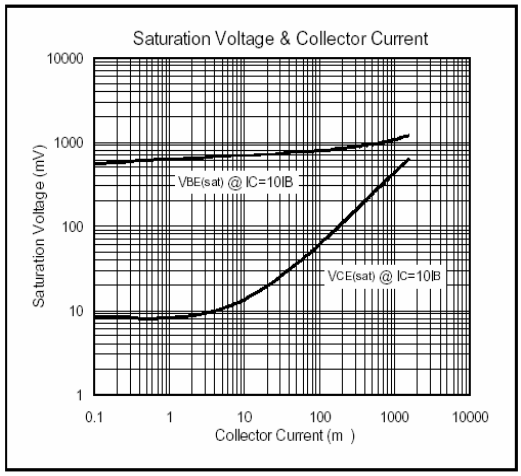
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

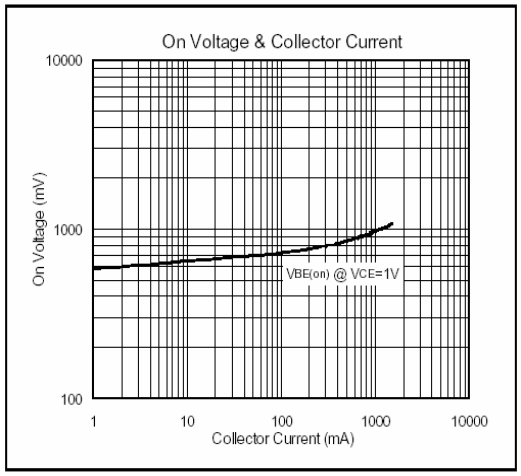
Classification Of $h_{FE}1$

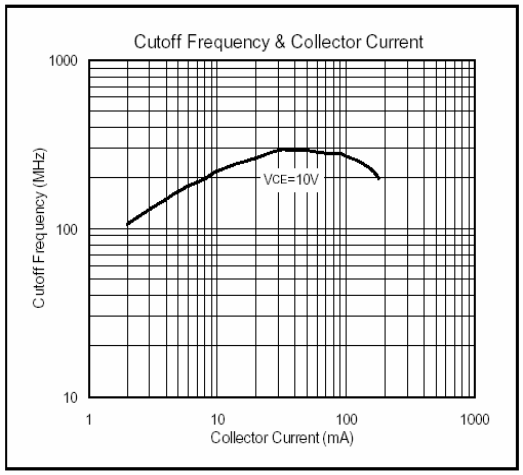
Rank	C	D	E
Range	120 ~ 200	160 ~ 320	250 ~ 500

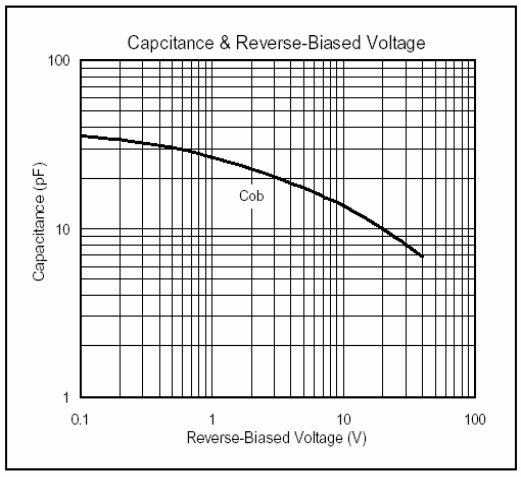
Characteristics Curve

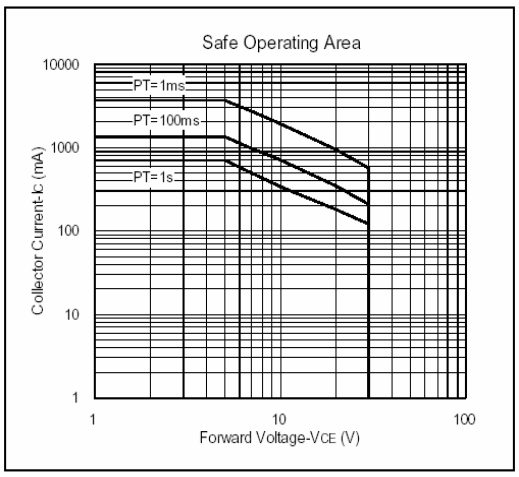












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